



2SB1260

PNP SILICON TRANSISTOR

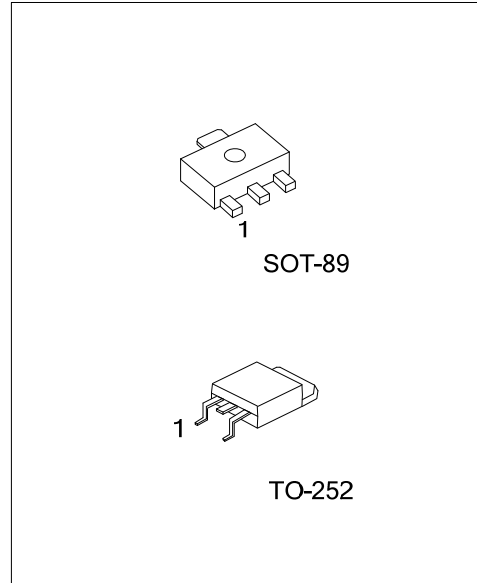
POWER TRANSISTOR

DESCRIPTION

The UTC **2SB1260** is a epitaxial planar type PNP silicon transistor.

FEATURES

- * High breakdown voltage and high current.
 $BV_{CEO} = -80V, I_C = -1A$
- * Good h_{FE} linearity.
- * Low $V_{CE(SAT)}$



Lead-free: 2SB1260L
 Halogen-free: 2SB1260G

ORDERING INFORMATION

Ordering Number			Package	Pin Assignment			Packing
Normal	Lead Free	Halogen Free		1	2	3	
2SB1260-x-AB3-R	2SB1260L-x-AB3-R	2SB1260G-x-AB3-R	SOT-89	B	C	E	Tape Reel
2SB1260-x-TN3-R	2SB1260L-x-TN3-R	2SB1260G-x-TN3-R	TO-252	B	C	E	Tape Reel

<p>2SB1260L-x-AB3-R</p>	<p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Rank</p> <p>(4)Lead Plating</p>	<p>(1) R: Tape Reel</p> <p>(2) AB3: SOT-89, TN3: TO-252</p> <p>(3) refer to Classification of h_{FE}</p> <p>(4) G: Halogen Free, L: Lead Free, Blank: Pb/Sn</p>
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■ ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector -Base Voltage	V _{CB0}	-80	V
Collector -Emitter Voltage	V _{CEO}	-80	V
Emitter -Base Voltage	V _{EBO}	-5	V
Peak Collector Current (single pulse, Pw=100ms)	I _{CM}	-2	A
DC Collector Current	I _C	-1	A
Power Dissipation	SOT-89	0.5	W
	TO-252	1.9	W
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-40 ~ +150	°C

Note 1. Printed circuit board, 1.7mm thick, collector copper plating 100mm² or larger.

2. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta= 25°C, unless otherwise specified)

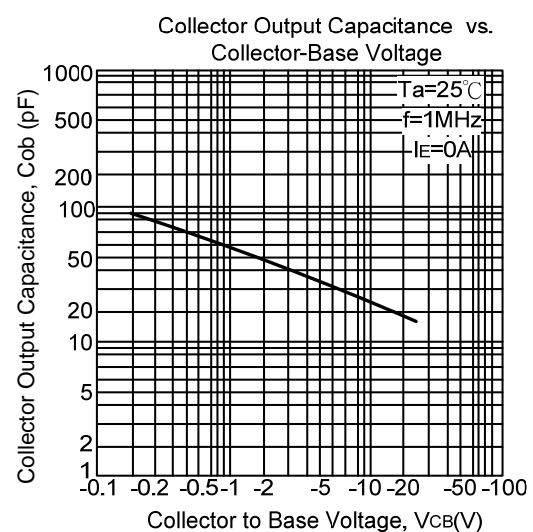
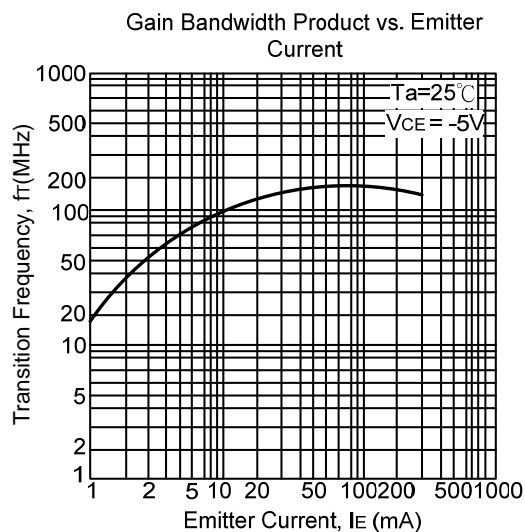
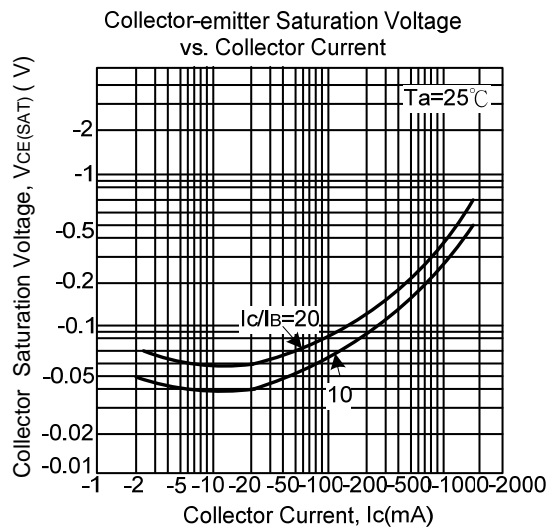
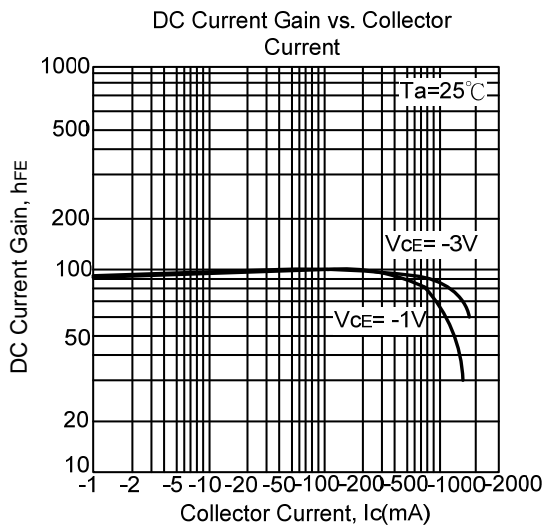
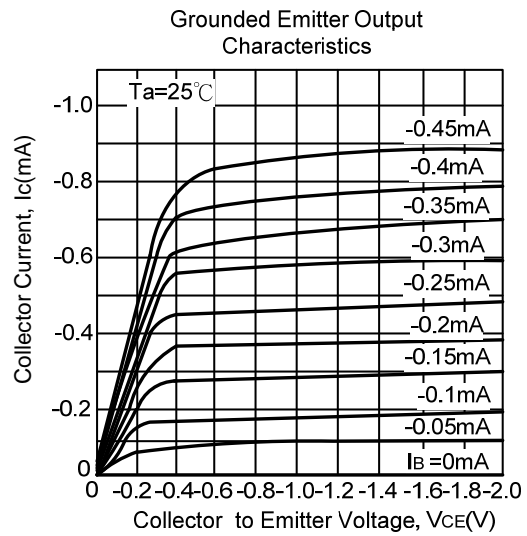
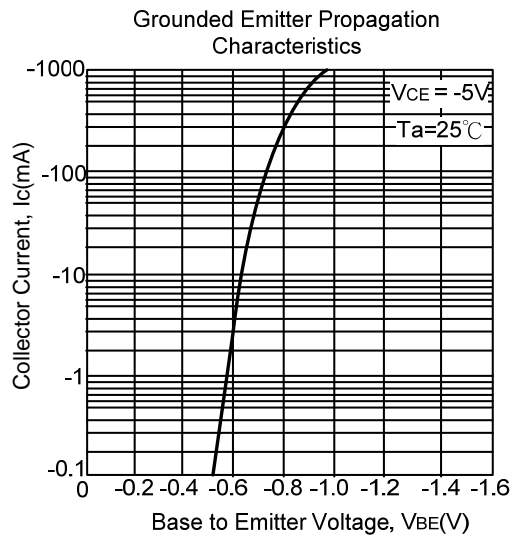
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Base Breakdown Voltage	BV _{CB0}	I _C = -50 μA	-80			V
Collector Emitter Breakdown Voltage	BV _{CEO}	I _C = -1mA	-80			V
Emitter Base Breakdown Voltage	BV _{EBO}	I _E = -50 μA	-5			V
Collector Cut-Off Current	I _{CB0}	V _{CB} =-60V			-1	μA
Emitter Cut-Off Current	I _{EBO}	V _{EB} =-4V			-1	μA
DC Current Gain(Note 1)	h _{FE}	V _{CE} =-3V, I _{OUT} =-0.1A	82		390	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =-500mA, I _B =-50mA			-0.4	V
Transition Frequency	f _T	V _{CE} = -5V, I _E =50mA, f=30MHz		100		MHz
Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		25		pF

Note 1: Pulse test: P_w<300μs, Duty Cycle<2%

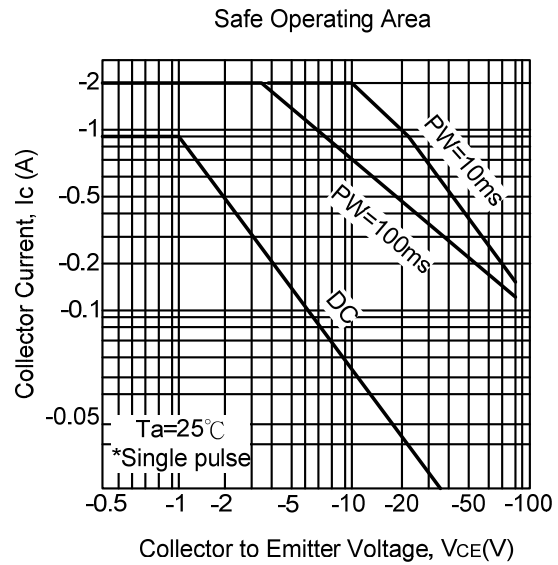
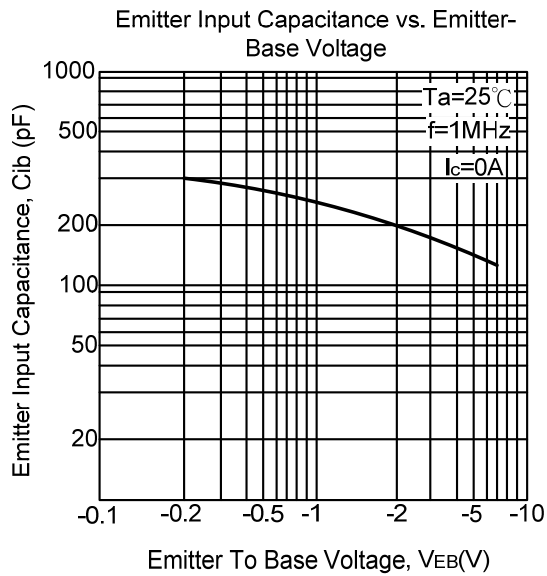
■ CLASSIFICATION OF h_{FE}

RANK	P	Q	R
RANGE	82 ~ 180	120 ~ 270	180 ~ 390

TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)



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